

Application No. 10/707,842

Applicant: Haining SUNG et al.

Title: METHOD AND APPARATUS FOR INCREASE STRAIN EFFECT
IN A TRANSISTOR CHANNEL

Responsive to Official Communication dated: December 27, 2005

REPLACEMENT SHEET

IAP7 Rec'd PCT/PTO 28 AUG 2006

Confirmation No. 1841

Attorney Docket No. P27165

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FIG. 1

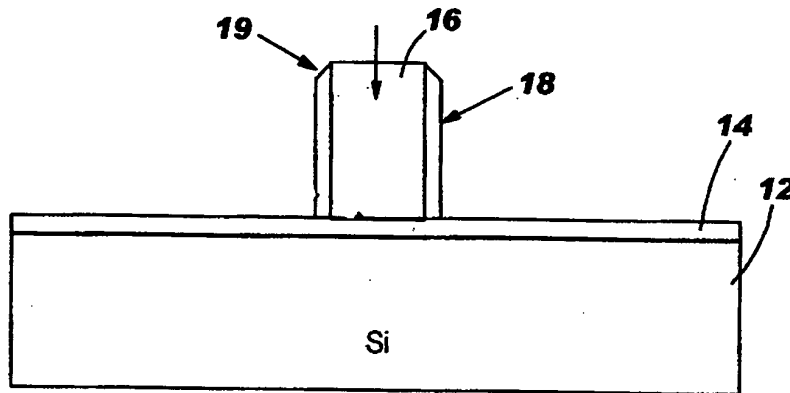
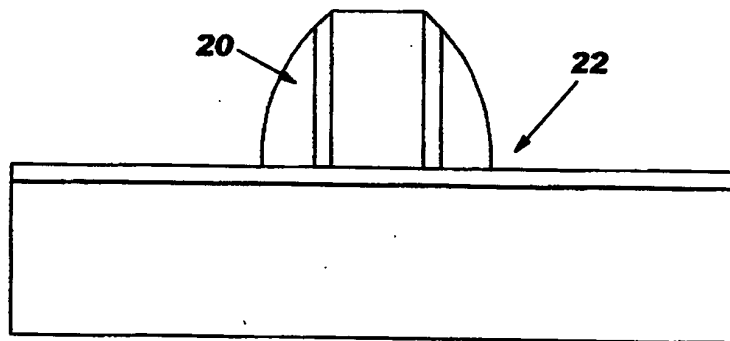


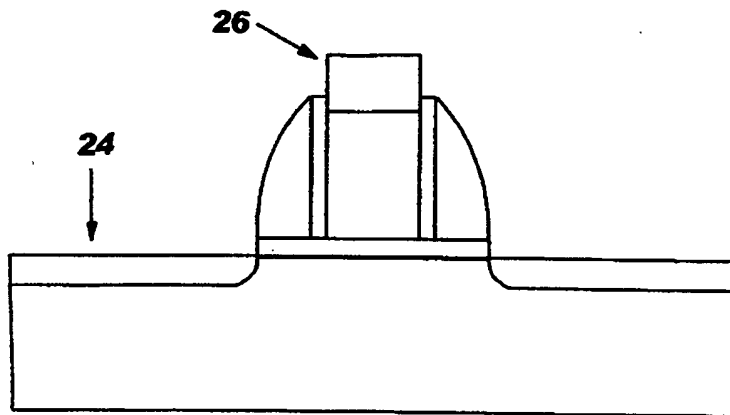
FIG. 2



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FIG. 3



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FIG. 4

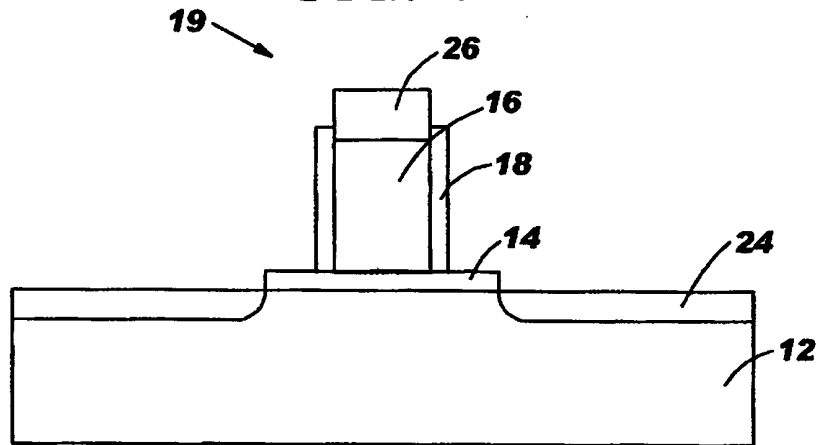
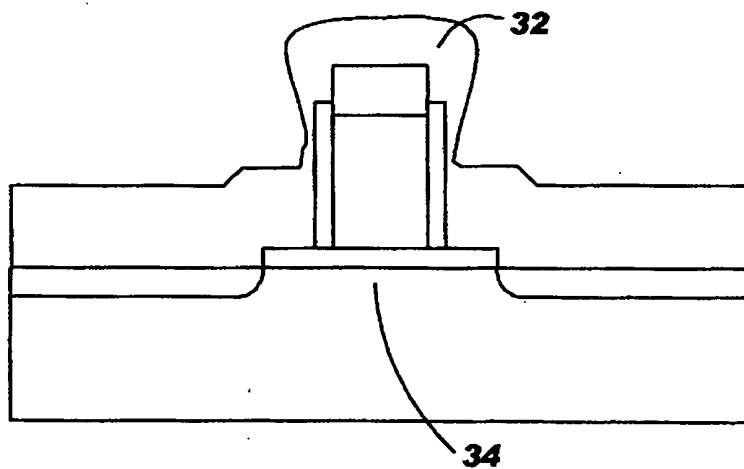


FIG. 5



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FIG. 6

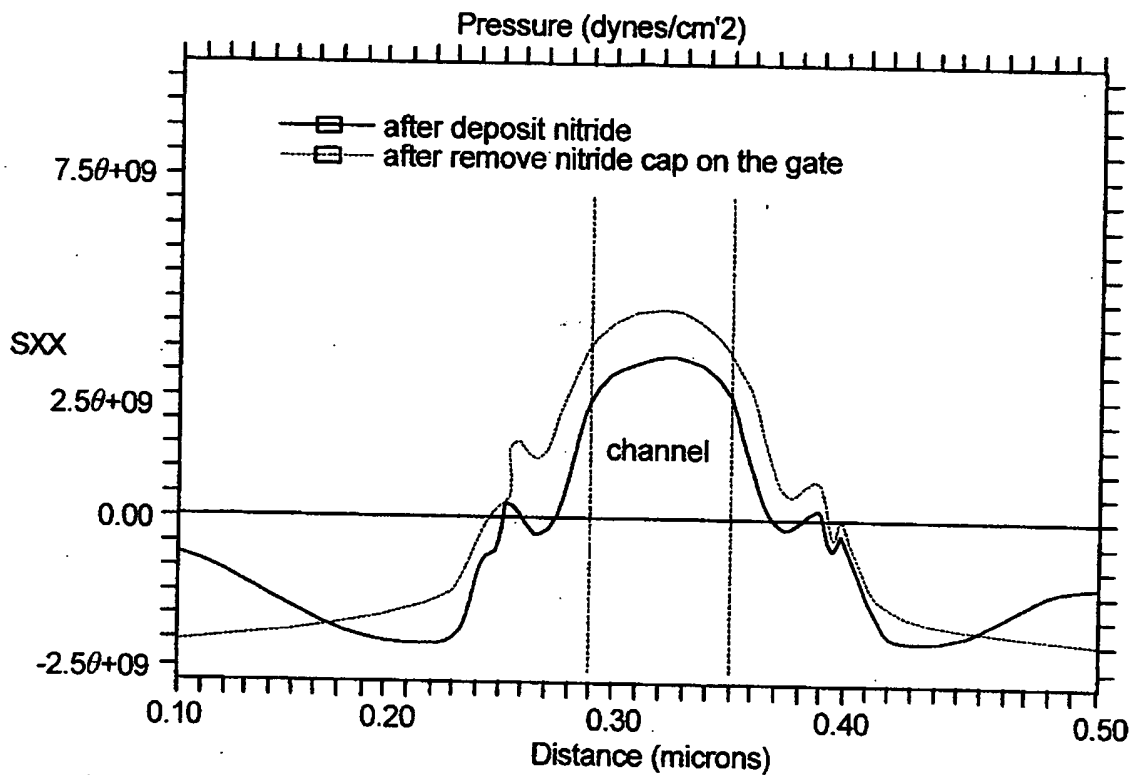
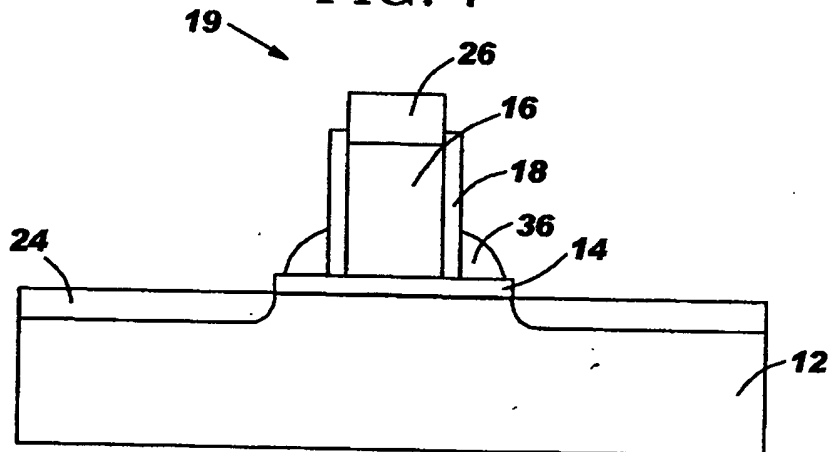


FIG. 7



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FIG. 8

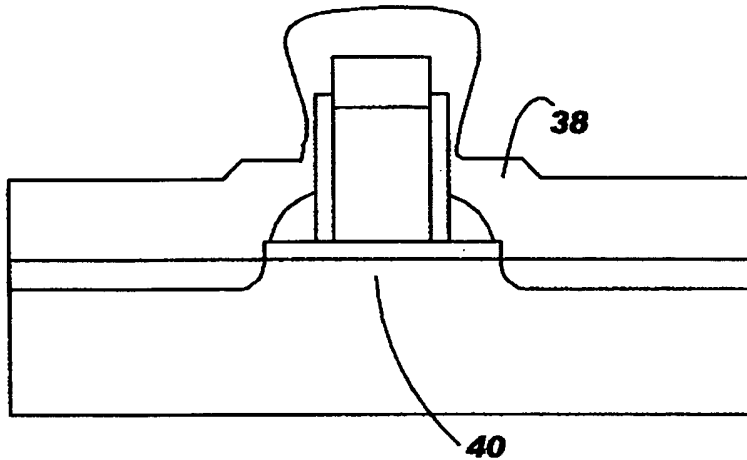
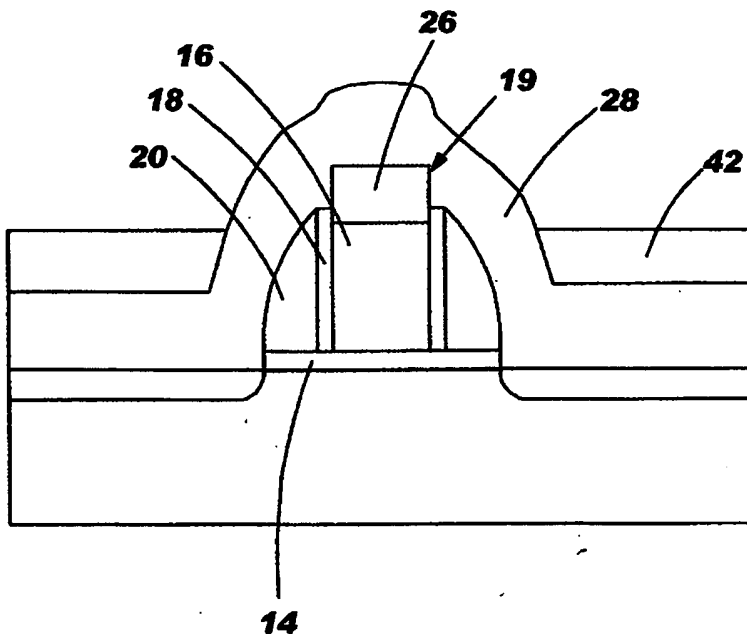


FIG. 9



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FIG. 10

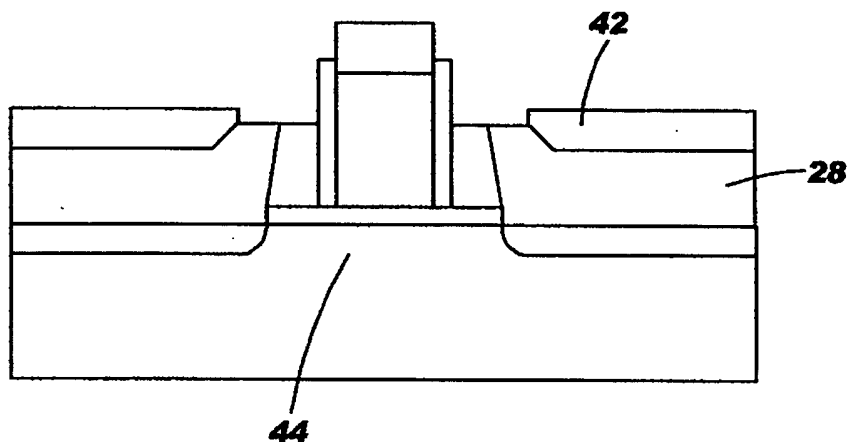
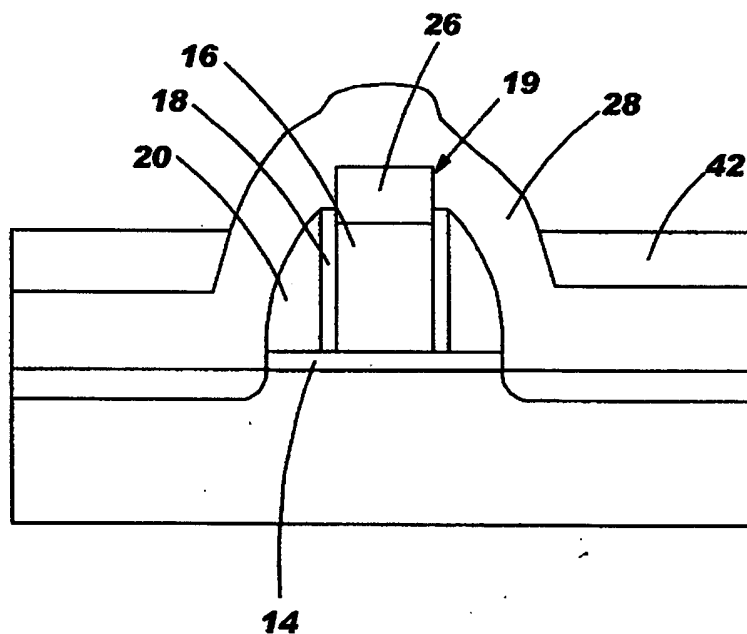


FIG. 11



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FIG. 12

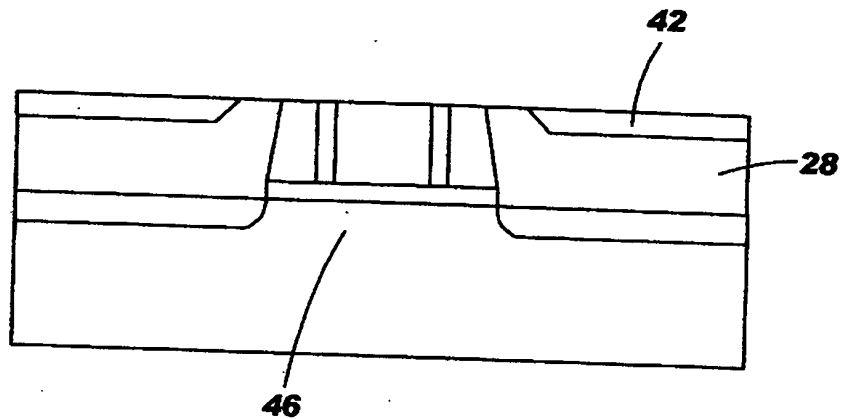
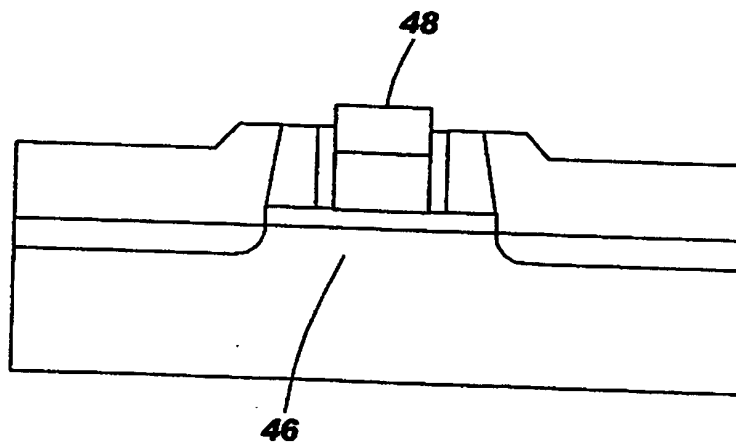


FIG. 13



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